

# BCR12CM-16LB

800V - 12A - Triac  
Medium Power Use

R07DS0976EJ0200  
Rev.2.00  
Feb 25, 2013

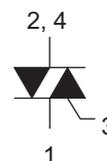
## Features

- $I_{T(RMS)}$  : 12 A
- $V_{DRM}$  : 800 V
- $I_{FGTB}$ ,  $I_{RGTB}$ ,  $I_{RGT III}$  : 30 mA
- The Product guaranteed maximum junction temperature 150°C
- Non-Insulated Type
- Planar Type

## Outline

RENESAS Package code: PRSS0004AG-A  
(Package name: TO-220AB)

RENESAS Package code: PRSS0004AA-A  
(Package name: TO-220)



1. T<sub>1</sub> Terminal
2. T<sub>2</sub> Terminal
3. Gate Terminal
4. T<sub>2</sub> Terminal

## Applications

Switching mode power supply, washing machine, motor control, heater control, and other general purpose control applications

## Maximum Ratings

Parameter	Symbol	Voltage class		Unit
		16		
Repetitive peak off-state voltage <sup>Note1</sup>	$V_{DRM}$	800		V
Non-repetitive peak off-state voltage <sup>Note1</sup>	$V_{DSM}$	960		V

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_{T(RMS)}$	12	A	Commercial frequency, sine full wave 360° conduction, $T_c = 123^{\circ}\text{C}$ <sup>Note3</sup>
Surge on-state current	$I_{TSM}$	120	A	60 Hz sinewave 1 full cycle, peak value, non-repetitive
$I^2t$ for fusion	$I^2t$	60	A <sup>2</sup> s	Value corresponding to 1 cycle of half wave 60 Hz, surge on-state current
Peak gate power dissipation	$P_{GM}$	5	W	
Average gate power dissipation	$P_{G(AV)}$	0.5	W	
Peak gate voltage	$V_{GM}$	10	V	
Peak gate current	$I_{GM}$	2	A	
Junction Temperature	$T_j$	-40 to +150	°C	
Storage temperature	$T_{stg}$	-40 to +150	°C	
Mass	—	2.1	g	Typical value

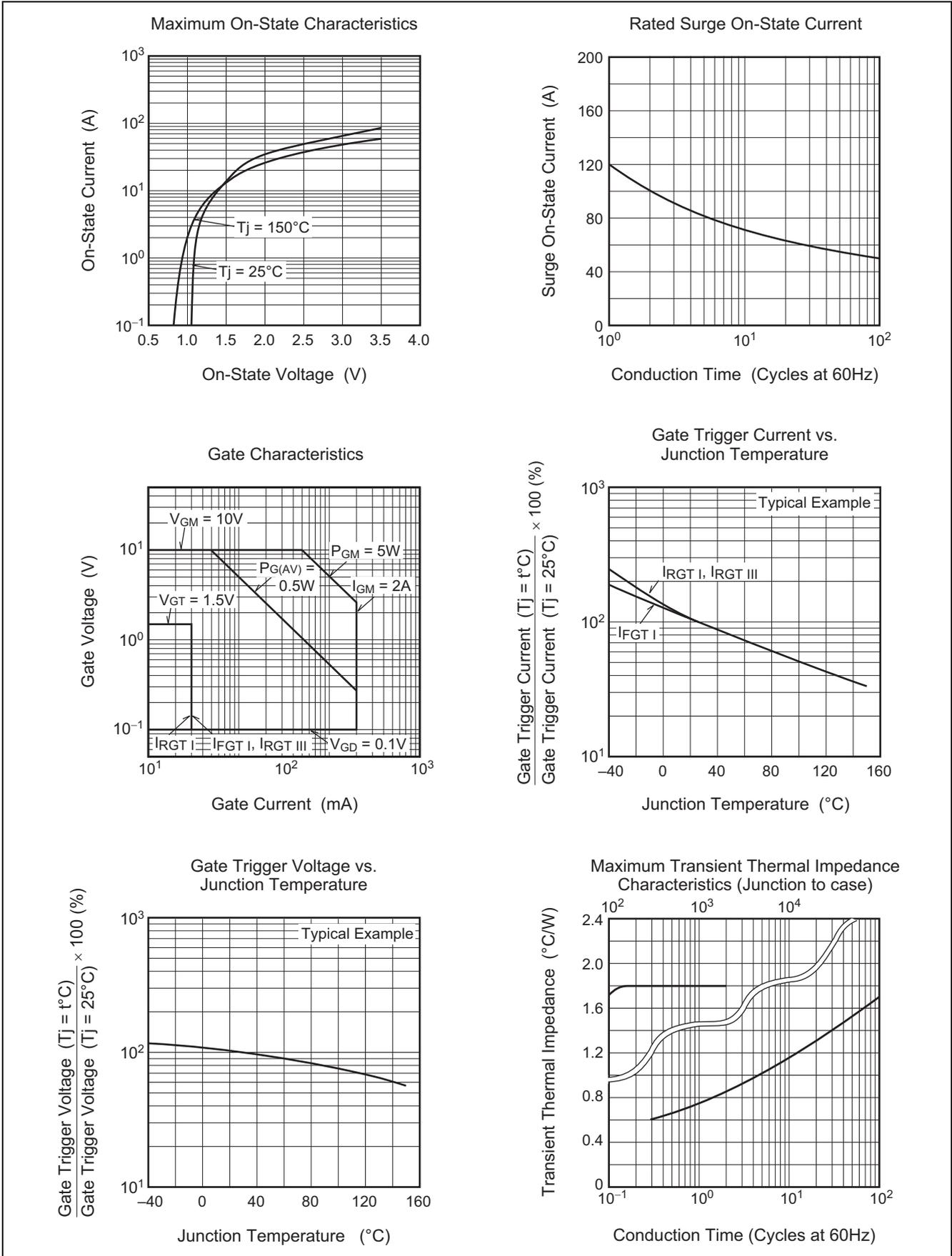
## Electrical Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Repetitive peak off-state current	$I_{DRM}$	—	—	2.0	mA	$T_j = 150^\circ\text{C}$ , $V_{DRM}$ applied
On-state voltage	$V_{TM}$	—	—	1.6	V	$T_c = 25^\circ\text{C}$ , $I_{TM} = 20\text{ A}$ , instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	I	$V_{FGTI}$	—	—	1.5	$T_j = 25^\circ\text{C}$ , $V_D = 6\text{ V}$ , $R_L = 6\ \Omega$ , $R_G = 330\ \Omega$
	II	$V_{RGTI}$	—	—	1.5	
	III	$V_{RGTIII}$	—	—	1.5	
Gate trigger current <sup>Note2</sup>	I	$I_{FGTI}$	—	—	30	$T_j = 25^\circ\text{C}$ , $V_D = 6\text{ V}$ , $R_L = 6\ \Omega$ , $R_G = 330\ \Omega$
	II	$I_{RGTI}$	—	—	30	
	III	$I_{RGTIII}$	—	—	30	
Gate non-trigger voltage	$V_{GD}$	0.2	—	—	V	$T_j = 125^\circ\text{C}$ , $V_D = 1/2 V_{DRM}$
		0.1	—	—	V	$T_j = 150^\circ\text{C}$ , $V_D = 1/2 V_{DRM}$
Thermal resistance	$R_{th(j-c)}$	—	—	1.8	$^\circ\text{C/W}$	Junction to case <sup>Note3,4</sup>
Critical-rate of rise of off-state commutation voltage <sup>Note5</sup>	$(dv/dt)_c$	10	—	—	V/ $\mu\text{s}$	$T_j = 125^\circ\text{C}$
		1	—	—	V/ $\mu\text{s}$	$T_j = 150^\circ\text{C}$

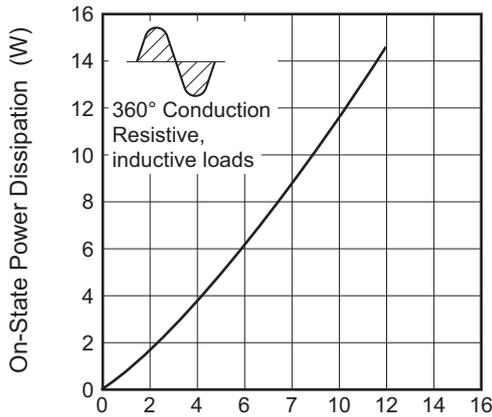
- Notes: 1. Gate open.  
 2. Measurement using the gate trigger characteristics measurement circuit.  
 3. Case temperature is measured at the  $T_2$  tab 1.5 mm apart from the molded case.  
 4. The contact thermal resistance  $R_{th(c-f)}$  in case of greasing is  $1.0^\circ\text{C/W}$ .  
 5. Test conditions of the critical-rate of rise of off-state commutation voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature $T_j = 125^\circ\text{C}/150^\circ\text{C}$ 2. Rate of decay of on-state commutating current $(di/dt)_c = -6\text{ A/ms}$ 3. Peak off-state voltage $V_D = 400\text{ V}$	

Performance Curves

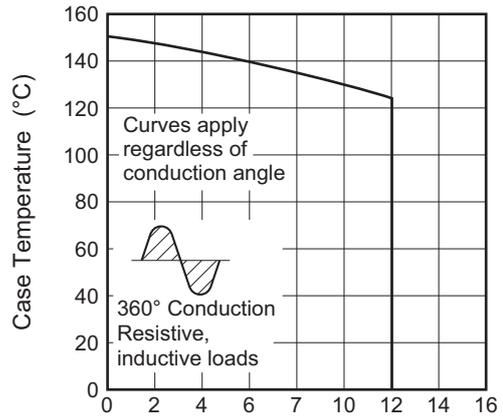


Maximum On-State Power Dissipation



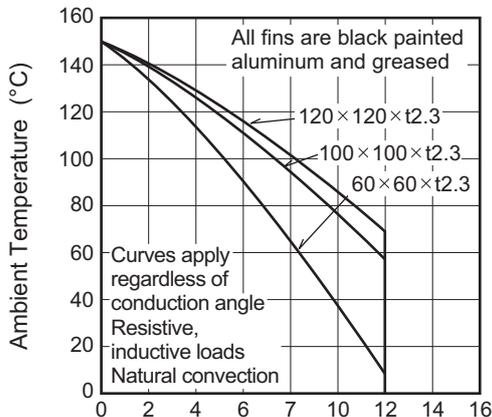
RMS On-State Current (A)

Allowable Case Temperature vs. RMS On-State Current



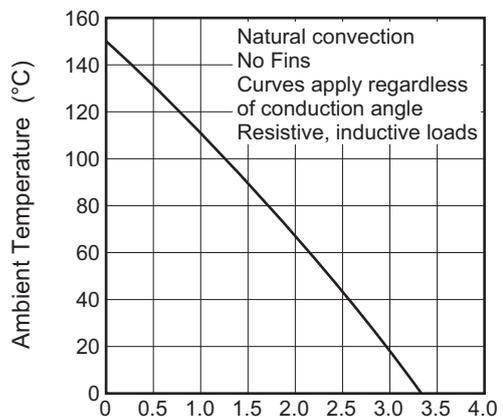
RMS On-State Current (A)

Allowable Ambient Temperature vs. RMS On-State Current



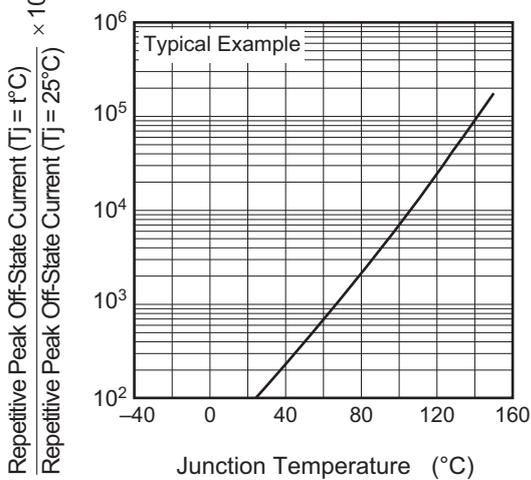
RMS On-State Current (A)

Allowable Ambient Temperature vs. RMS On-State Current

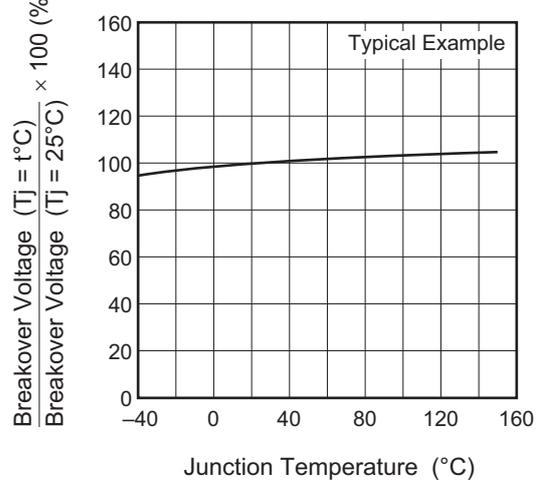


RMS On-State Current (A)

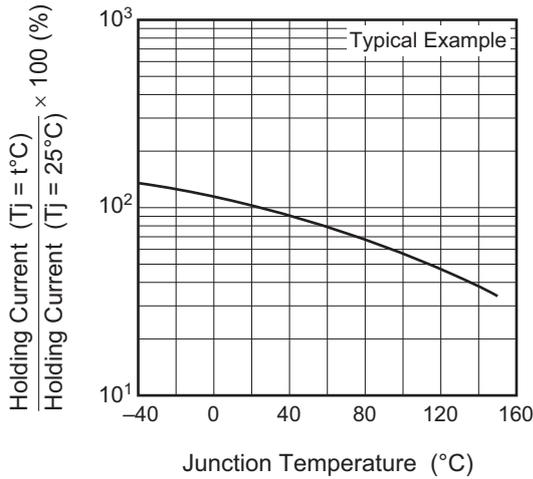
Repetitive Peak Off-State Current vs. Junction Temperature



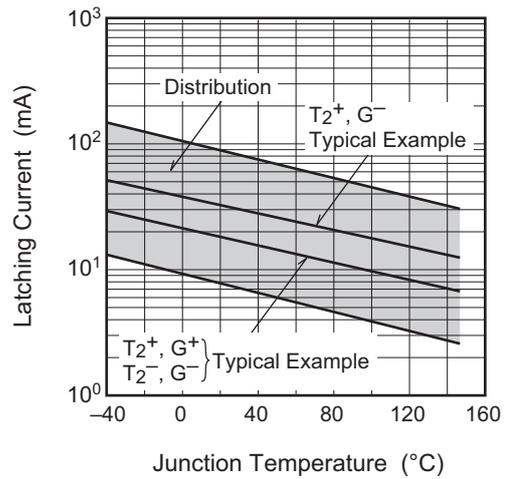
Breakover Voltage vs. Junction Temperature



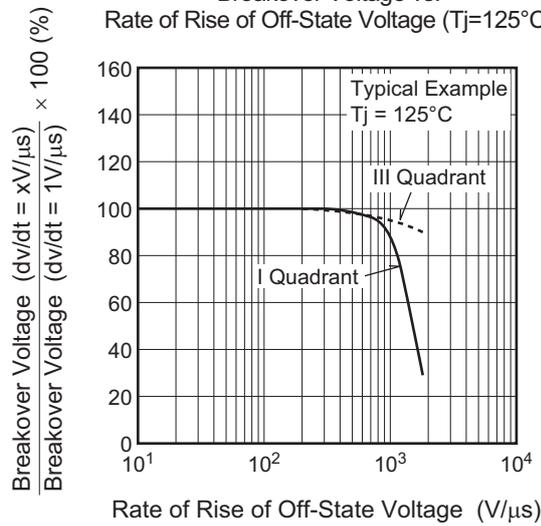
Holding Current vs. Junction Temperature



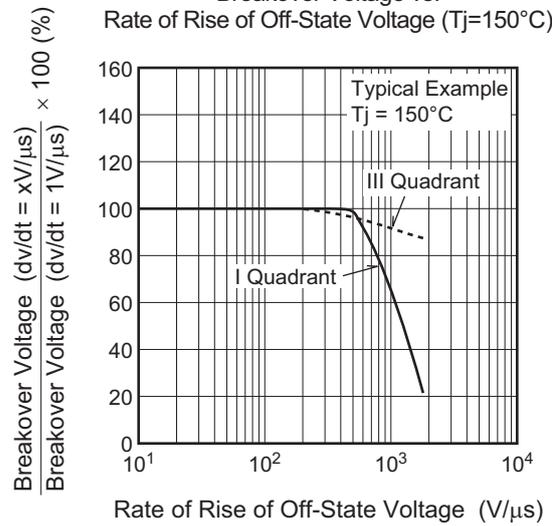
Latching Current vs. Junction Temperature



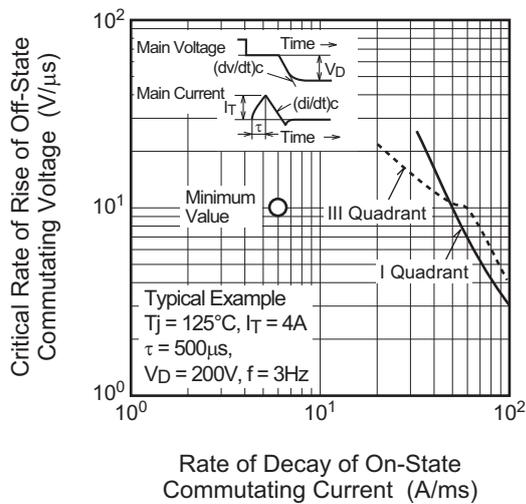
Breakover Voltage vs. Rate of Rise of Off-State Voltage (Tj=125°C)



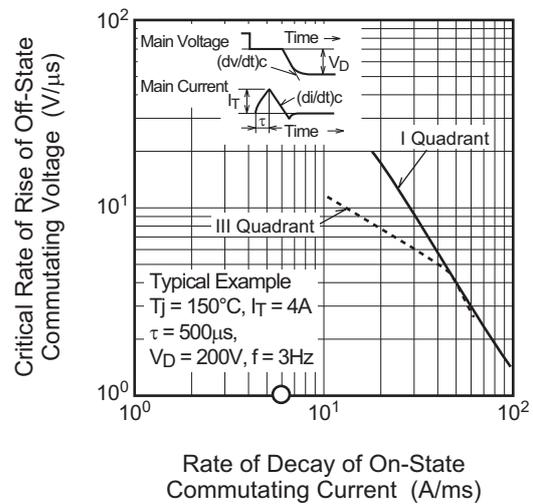
Breakover Voltage vs. Rate of Rise of Off-State Voltage (Tj=150°C)



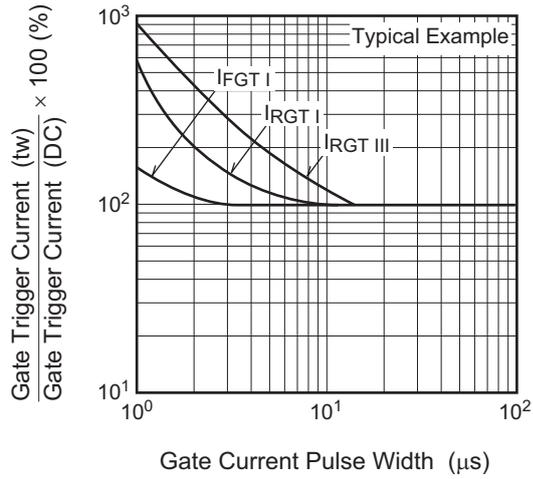
Commutation Characteristics (Tj=125°C)



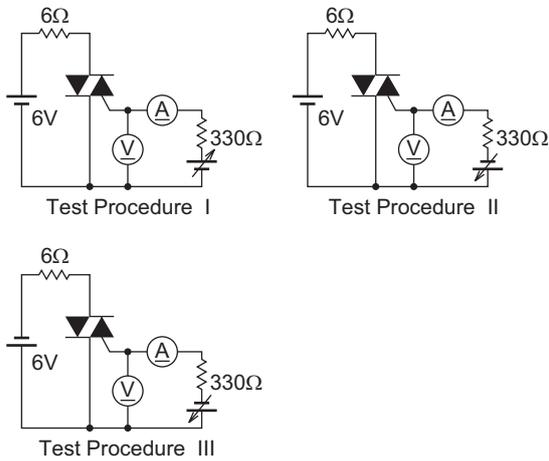
Commutation Characteristics (Tj=150°C)



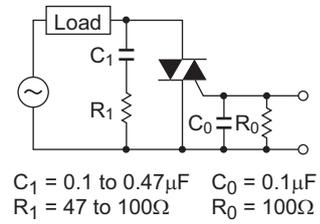
Gate Trigger Current vs. Gate Current Pulse Width



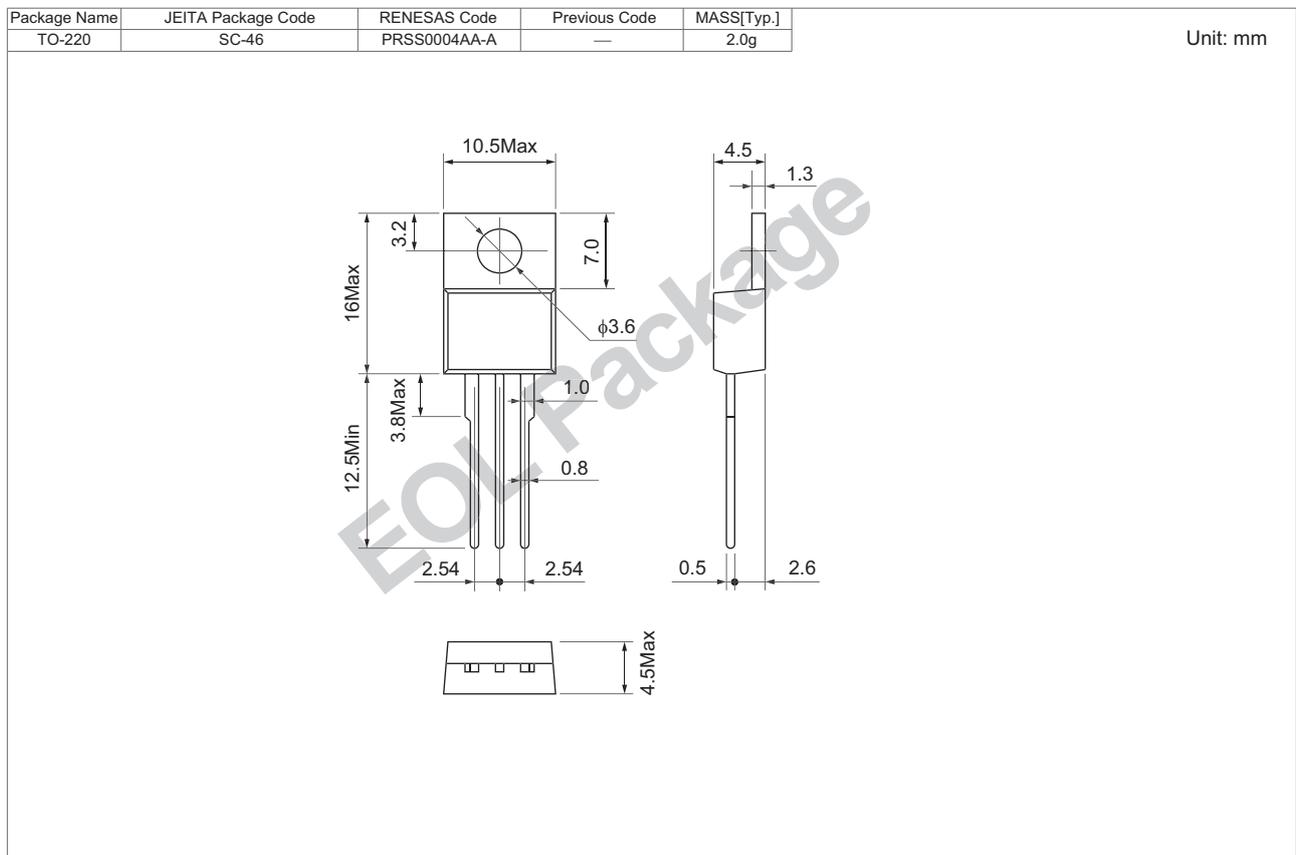
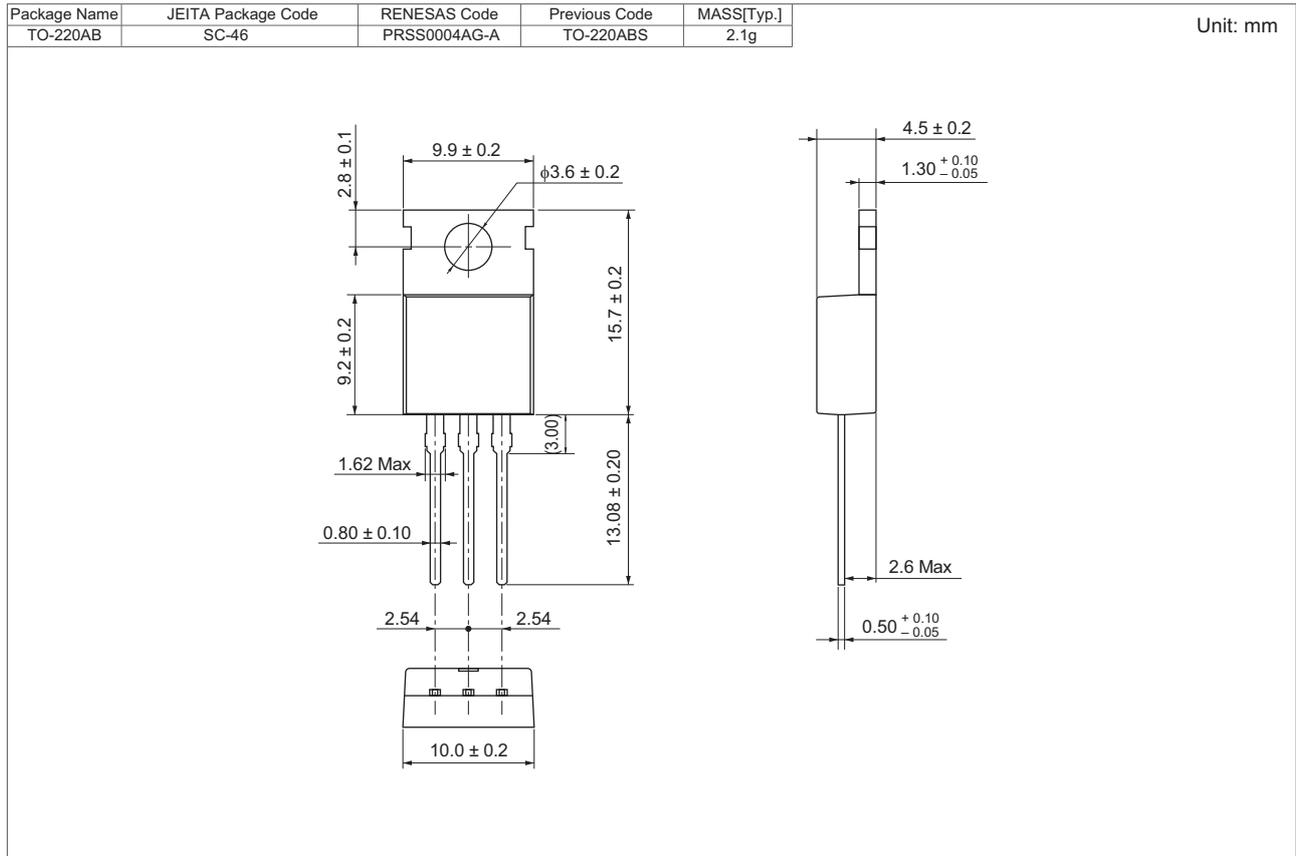
Gate Trigger Characteristics Test Circuits



Recommended Circuit Values Around The Triac



Package Dimensions



**Ordering Information**

<b>Orderable Part Number</b>	<b>Packing</b>	<b>Quantity</b>	<b>Remark</b>
BCR12CM-16LB#BB0	Tube	50 pcs.	Straight type
BCR12CM-16LBA8#BB0	Tube	50 pcs.	A8 Lead form

Note: Please confirm the specification about the shipping in detail.

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